Kentaro Kaneko

List of Publications by Year
in descending order

67	1,840	236925 25	276875 41
papers	citations	h-index	g-index

68	68	68	909
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Novel p-type oxides with corundum structure for gallium oxide electronics. Journal of Materials Research, 2022, 37, 651-659.	2.6	7
2	Prospects for phase engineering of semi-stable Ga2O3 semiconductor thin films using mist chemical vapor deposition. Journal of Applied Physics, 2022, 131, .	2.5	31
3	Analysis of Deep Traps in Mist Chemical Vapor Depositionâ€Grown nâ€Type Î±â€Ga₂O₃ by Photocapacitance Method. Physica Status Solidi (B): Basic Research, 2021, 258, 2000622.	1.5	6
4	Thermal stability of Î±-(Al_xGa_{1â€“x})₂O₃films grown on c-plane sapphire substrates with an Al composition up to 90%. Japanese Journal of Applied Physics, 2021, 60, SBBD13.	1.5	13
5	Ultra-wide bandgap corundum-structured p-type Î± -(Ir,Ga)2O3 alloys for Î± -Ga2O3 electronics. Applied Physics Letters, 2021, 118, .	3.3	36
6	Initial nucleation scheme of Ga₂O₃ on (0001) sapphire by mist CVD for the growth of Î±-phase. Japanese Journal of Applied Physics, 2021, 60, 055501.	1.5	13
7	Synthesis of Metastable or Non-Equilibrium-Phased Oxides by the Mist CVD method. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 369-373.	0.2	1
8	Establishment of a growth route of crystallized rutile GeO2 thin film (â‰§1 Î¼m/h) and its structural properties. Applied Physics Letters, 2021, 119, .	3.3	18
9	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. Applied Physics Letters, 2021, 119, .	3.3	7
10	Research of Semiconductor Materials That Emit in the Vacuum Ultraviolet Region of 200 nm or Less. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 727-731.	0.2	0
11	Thermal stability of Î±-Ga2O3 films grown on c-plane sapphire substrates via mist-CVD. AIP Advances, 2020, 10, .	1.3	26
12	Impact of hydrochloric acid on the epitaxial growth of In₂O₃ films on (0001)Î±-Al₂O₃ substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.	2.4	6
13	Synthesis of High-Quality Î±-Ga₂O₃ thin films on Sapphire Substrates with Introduction of Buffer Layers. Zairyo/Journal of the Society of Materials Science, Japan, 2020, 69, 707-711.	0.2	0
14	Enhancement of epitaxial lateral overgrowth in the mist chemical vapor deposition ofÎ±-Ga₂O₃by using a-plane sapphire substrate. Japanese Journal of Applied Physics, 2019, 58, 120912.	1.5	28
15	Pure deep-ultraviolet cathodoluminescence from rocksalt-structured MgZnO grown with carbon-free precursors. Applied Physics Express, 2019, 12, 052011.	2.4	18
16	An Nightmare of the Day before Christmas Eve. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 731-732.	0.2	0
17	Synthesis of Metastable or Non-Equilibrium Phased Oxides and Their Physical Properties. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 733-738.	0.2	0
18	A power device material of corundum-structured Î±-Ga₂O₃fabricated by MIST EPITAXY^{Â®}technique. Japanese Journal of Applied Physics, 2018, 57, 02CB18.	1.5	76

#	Article	IF	Citations
19	Electrical characterization of Si-doped n-type Î±-Ga2O3 on sapphire substrates. MRS Advances, 2018, 3, 171-177.	0.9	41
20	Control of Crystal Structure of Ga₂O₃ on Sapphire Substrate by Introduction of Î±â€(Al_xGa_{1â^'x})₂O₃ Buffer Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700326.	1.5	41
21	Evaluation of band alignment of Î±-Ga₂O₃/Î±-(Al_xGa_{1â^'}_x)₂O₃ by X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 040314.	1.5	46
22	Electrical properties of Î±-Ir2O3/Î±-Ga2O3 pn heterojunction diode and band alignment of the heterostructure. Applied Physics Letters, 2018, 113, .	3.3	74
23	Study on corundum-structured p-type iridium oxide thin films and band alignment at iridium oxide /gallium oxide hetero-junction. , 2018, , .		2
24	Tin oxide coating by nonvacuum-based mist chemical vapor deposition on stainless steel separators for polymer electrolyte fuel cells. Japanese Journal of Applied Physics, 2018, 57, 117103.	1.5	22
25	Deep-Ultraviolet Luminescence of Rocksalt-Structured MgxZn1â^'xO (xâ€‰>â€‰0.5) Films on MgO Substrates. Journal of Electronic Materials, 2018, 47, 4356-4360.	2.2	15
26	Unpredicted surface termination of Î±-Fe 2 O 3 (0001) film grown by mist chemical vapor deposition. Surface Science, 2017, 660, 9-15.	1.9	9
27	Corundum-Structured Î±-In2O3 as a Wide-Bandgap Semiconductor for Electrical Devices. MRS Advances, 2017, 2, 301-307.	0.9	6
28	Corundum-strructured Î±-Ga<inf>2</inf>O<inf>3</inf>-based alloys for future power device applications. , 2017, , .		1
29	Recent Advancement of Semiconductor Materials and Devices. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 58-65.	0.2	3
30	Metal Separator of Fuel Cells Coated with Highly Conductive and Highly Corrosion-Resistant Oxide Thin Films. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 639-643.	0.2	3
31	Ga₂O₃ Crystal for Power Device. Journal of the Institute of Electrical Engineers of Japan, 2017, 137, 693-696.	0.0	0
32	Crystal Growth and Device Applications of Corundum-Structured Gallium Oxide. Zairyo/Journal of the Society of Materials Science, Japan, 2016, 65, 631-637.	0.2	0
33	Characterization of band offset in Î±-(Al<inf>x</inf>Ga<inf>1-x</inf>)<inf>2</inf>O<inf>3</inf>/ Î±-Ga<inf>2</inf>O<inf>3</inf> heterostructures. , 2016, , .		1
34	Surface termination structure of Î±-Ga2O3 film grown by mist chemical vapor deposition. Applied Physics Letters, 2016, 108, 251602.	3.3	25
35	Evolution of corundum-structured III-oxide semiconductors: Growth, properties, and devices. Japanese Journal of Applied Physics, 2016, 55, 1202A3.	1.5	106
36	Homoepitaxial growth of beta gallium oxide films by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 1202B8.	1.5	79

#	Article	IF	Citations
37	Fabrication of Î±-Ga<inf>2</inf>O<inf>3</inf> thin films using properties. , 2016, , .		0
38	Conductivity control of Sn-doped Î±-Ga₂O₃ thin films grown on sapphire substrates. Japanese Journal of Applied Physics, 2016, 55, 1202BA.	1.5	91
39	Growth of rocksalt-structured Mg_xZn_{1âˆ’} _xO (x > 0.5) films on MgO substrates and their deep-ultraviolet luminescence. Applied Physics Express, 2016, 9, 111102.	2.4	26
40	Crack-free thick (âˆ¼5 Âµm) Î±-Ga₂O₃ films on sapphire substrates with Î±-(Al,Ga)₂O₃ buffer layers. Japanese Journal of Applied Physics, 2016, 55, 1202B4.	1.5	32
41	Reduction in edge dislocation density in corundum-structured Î±-Ga₂O₃ layers on sapphire substrates with quasi-graded Î±-(Al,Ga)₂O₃ buffer layers. Applied Physics Express, 2016, 9, 071101.	2.4	76
42	Growth characteristics of corundum-structured Î±-(Al Ga1âˆ’)2O3/Ga2O3 heterostructures on sapphire substrates. Journal of Crystal Growth, 2016, 436, 150-154.	1.5	72
43	Vertical Schottky barrier diodes of α-Ga<inf>2</inf>O<inf>3</inf> fabricated by mist epitaxy. , 2015, , .		6
44	Growth and metalâ€“oxideâ€“semiconductor field-effect transistors of corundum-structured alpha indium oxide semiconductors. Applied Physics Express, 2015, 8, 095503.	2.4	19
45	Fabrication of Cu₂ZnSnS₄ Thin Films by Ultrasonic-Atomized Mist Methods. Zairyo/Journal of the Society of Materials Science, Japan, 2015, 64, 410-413.	0.2	4
46	Enhanced thermal stability of alpha gallium oxide films supported by aluminum doping. Japanese Journal of Applied Physics, 2015, 54, 030301.	1.5	50
47	Faraday effect of bismuth iron garnet thin film prepared by mist CVD method. Japanese Journal of Applied Physics, 2015, 54, 063001.	1.5	14
48	Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films. Journal of Crystal Growth, 2014, 401, 588-592.	1.5	129
49	Ultrasonicâ€assisted mist chemical vapor deposition of IIâ€oxide and related oxide compounds. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1225-1228.	0.8	28
50	Preparation of yttrium iron garnet thin films by mist chemical vapor deposition method and their magneto-optical properties. Japanese Journal of Applied Physics, 2014, 53, 05FB17.	1.5	8
51	Growth of corundum-structured (In Ga1âˆ’)2O3 alloy thin films on sapphire substrates with buffer layers. Journal of Crystal Growth, 2014, 401, 670-672.	1.5	46
52	Band gap and function engineering for novel functional alloy semiconductors: Bloomed as magnetic properties at room temperature with Î±-(GaFe)2O3. Journal of Applied Physics, 2013, 113, .	2.5	62
53	Growth of corundum-structured In2O3 thin films on sapphire substrates with Fe2O3 buffer layers. Journal of Crystal Growth, 2013, 364, 30-33.	1.5	62
54	Fabrication of Corundum-Structured Î±-(InFe)2O3 Alloy Films on Sapphire Substrates by Inserting Î±-Fe2O3 Buffer Layer. Materials Research Society Symposia Proceedings, 2013, 1494, 221-225.	0.1	1

#	Article	IF	Citations
55	Crystal Structure of Non-Doped and Sn-Doped Î±-(GaFe)2O3 Thin Films.. Materials Research Society Symposia Proceedings, 2013, 1494, 147-152.	0.1	3
56	Oriented growth of beta gallium oxide thin films on yttriumâ€stabilized zirconia substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1596-1599.	0.8	23
57	Evaluation of Misfit Relaxation in Î±-Ga₂O₃ Epitaxial Growth on Î±-Al₂O₃ Substrate. Japanese Journal of Applied Physics, 2012, 51, 020201.	1.5	63
58	Growth and Band Gap Control of Corundum-Structured Î±-(AlGa)₂O₃ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 100207.	1.5	83
59	Evaluation of Misfit Relaxation in Î±-Ga₂O₃Epitaxial Growth on Î±-Al₂O₃Substrate. Japanese Journal of Applied Physics, 2012, 51, 020201.	1.5	20
60	Growth and Band Gap Control of Corundum-Structured Î±-(AlGa)₂O₃Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 100207.	1.5	29
61	Fabrication of Lithium-Based Oxide Thin Films by Ultrasonic-Assisted Mist CVD Technique. Zairyo/Journal of the Society of Materials Science, Japan, 2011, 60, 994-997.	0.2	3
62	Corundumâ€structured Î±â€phase Ga₂O₃â€Cr₂O₃â€Fe₂O₃ alloy system for novel functions. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2467-2470.	0.8	35
63	Fabrication by Mist CVD Method and Evaluation of Corundum Structured Oxide Semiconductor Thin Films. Zairyo/Journal of the Society of Materials Science, Japan, 2010, 59, 686-689.	0.2	4
64	Mist Deposition Technique as a Green Chemical Route for Synthesizing Oxide and Organic Thin Films. Materials Research Society Symposia Proceedings, 2009, 1220, 4061.	0.1	3
65	Fabrication of Highly Crystalline Corundum-Structured Î±-(Ga_{1-x}Fe_x)₂O₃Alloy Thin Films on Sapphire Substrates. Applied Physics Express, 0, 2, 075501.	2.4	83
66	Mist Chemical Vapor Deposition Growth of Î±â€In 2 O 3 Films Using Indium Oxide Powder as Source Precursor. Physica Status Solidi (B): Basic Research, 0, , 2100414.	1.5	3
67	VUV emission properties of rocksaltâ€structured MgZnO microcrystals prepared on quartz glass substrates. Physica Status Solidi (B): Basic Research, 0, , 2100354.	1.5	1